

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

Silicon Controlled Rectifiers Reverse Blocking Triode Thyristors

... multi-purpose PNP silicon controlled rectifiers suited for industrial, consumer, and military applications. Offered in a choice of space-saving, economical packages for mounting versatility.

- Uniform Low-Level Noise-Immune Gate Triggering — $I_{GT} = 10 \text{ mA (Typ) @ } T_C = 25^\circ\text{C}$
- Low Forward "On" Voltage — $V_T = 1 \text{ V (Typ) @ 5 Amp @ } 25^\circ\text{C}$
- High Surge-Current Capability — $I_{TSM} = 100 \text{ Amp Peak}$
- Shorted Emitter Construction

MAXIMUM RATINGS (Apply over operating temperature range and for all case types unless otherwise noted.)

Rating	Symbol	Value	Unit
*Peak Repetitive Forward and Reverse Blocking Voltage, Note 1	V_{DRM} or V_{RRM}	50 100 200 400 600	Volts
Forward Current RMS	$I_T(\text{RMS})$	8	Amps
*Peak Forward Surge Current (One cycle, 60 Hz, $T_J = -40$ to $+100^\circ\text{C}$)	I_{TSM}	100	Amps
Circuit Fusing ($t = 8.3 \text{ ms}$)	I^2t	40	A^2s
*Peak Gate Power	P_{GM}	6	Watts
*Average Gate Power	$P_{G(AV)}$	0.5	Watt
*Peak Gate Current	I_{GM}	2	Amps
Peak Gate Voltage, Note 2	V_{GM}	10	Volts
*Operating Temperature Range	T_J	-40 to $+100$	$^\circ\text{C}$
*Storage Temperature Range	T_{stg}	-40 to $+150$	$^\circ\text{C}$
Stud Torque		15	In. lb.

**2N4168
thru
2N4174
2N4184
thru
2N4190**

**SCRs
8 AMPERES RMS
50 thru 600 VOLTS**



CASE 68-01

2N4168 thru 2N4174



CASE 87L-02

2N4184 thru 2N4190



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	2.5*	$^{\circ}C/W$
Thermal Resistance, Case to Ambient (See Figure 11) 2N4183-98	$R_{\theta CA}$	50	—	$^{\circ}C/W$

*Indicates JEDEC Registered Data.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
*Peak Forward or Reverse Blocking Current (Rated V_{DRM} or V_{RRM} , gate open) $T_C = 25^{\circ}C$ $T_C = 100^{\circ}C$	I_{DRM} , I_{RRM}	— —	— —	10 2	μA mA
Gate Trigger Current (Continuous dc), Note 1 ($V_D = 7 V_{DO}$, $R_L = 100 \Omega$) *($V_D = 7 V_{DO}$, $R_L = 100 \Omega$, $T_C = -40^{\circ}C$)	I_{GT}	— —	10 —	30 60	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 7 V_{DO}$, $R_L = 100 \Omega$) *($V_D = 7 V_{DO}$, $R_L = 100 \Omega$, $T_C = -40^{\circ}C$) *($V_D = 7 V_{DO}$, $R_L = 100 \Omega$, $T_C = 100^{\circ}C$)	V_{GT}	— — 0.2	0.75 — —	1.5 2.5 —	Volts
*Forward "On" Voltage (pulsed, 1 ms max, duty cycle $\leq 1\%$) ($I_{TM} = 15.7 A$)	V_{TM}	—	1.4	2	Volts
Holding Current ($V_D = 7 V_{DO}$, gate open) *($V_D = 7 V_{DO}$, gate open, $T_C = -40^{\circ}C$)	I_H	— —	10 —	30 60	mA
Turn-On Time ($t_d + t_r$) ($I_G = 20 mA$, $I_F = 5 A$, $V_D = \text{Rated } V_{DRM}$)	t_{on}	—	1	—	μs
Turn-Off Time ($I_F = 5 A$, $I_R = 5 A$) ($I_F = 5 A$, $I_R = 5 A$, $T_C = 100^{\circ}C$, $V_D = \text{Rated } V_{DRM}$) ($dv/dt = 30 V/\mu s$)	t_{off}	— —	15 25	— —	μs
Forward Voltage Application Rate (Exponential) (Gate open, $T_C = 100^{\circ}C$, $V_D = \text{Rated } V_{DRM}$)	dv/dt	—	50	—	$V/\mu s$